Nov. 2005

THE SPECIFICATION OF AlGaAs IR LED CHIP "YL-C660nM-35mcd"

1. DESCRIPTION

This is a AlGaAs red LED chip. It is N-side up.

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION			MIN.	TYP.	MAX.	UNIT
Forward Voltage	(Vf)	IF=20mA		1.8		V
Reverse Voltage	(Vr)	IR=10uA	5			V
luminous intensity[1)]	(Iv)	IF=20mA	35			mcd
Peak Wavelength	(λp)	IF=20mA	640		670	nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current : 50 mA(DC)
Reverse Voltage : 5 V(IR=10uA)
Storage Temperature
while on mylar membrane : 0 to 40 deg. C
after removal from mylar membrane : -30 to 100 deg. C

4. PHYSICAL CHRACTERISTICS AND STRUCTURE

1) Material : AlGaAs
2) Structure : Double Hetero Structure
3) Junction Size : 0.280mmx0.280mm
4) Thickness : 0.160mm
5) Bond Pad Size : 0.140mm diameter
6) Anode Metallization : Gold Alloy
7) Cathode Metallization : Gold Alloy

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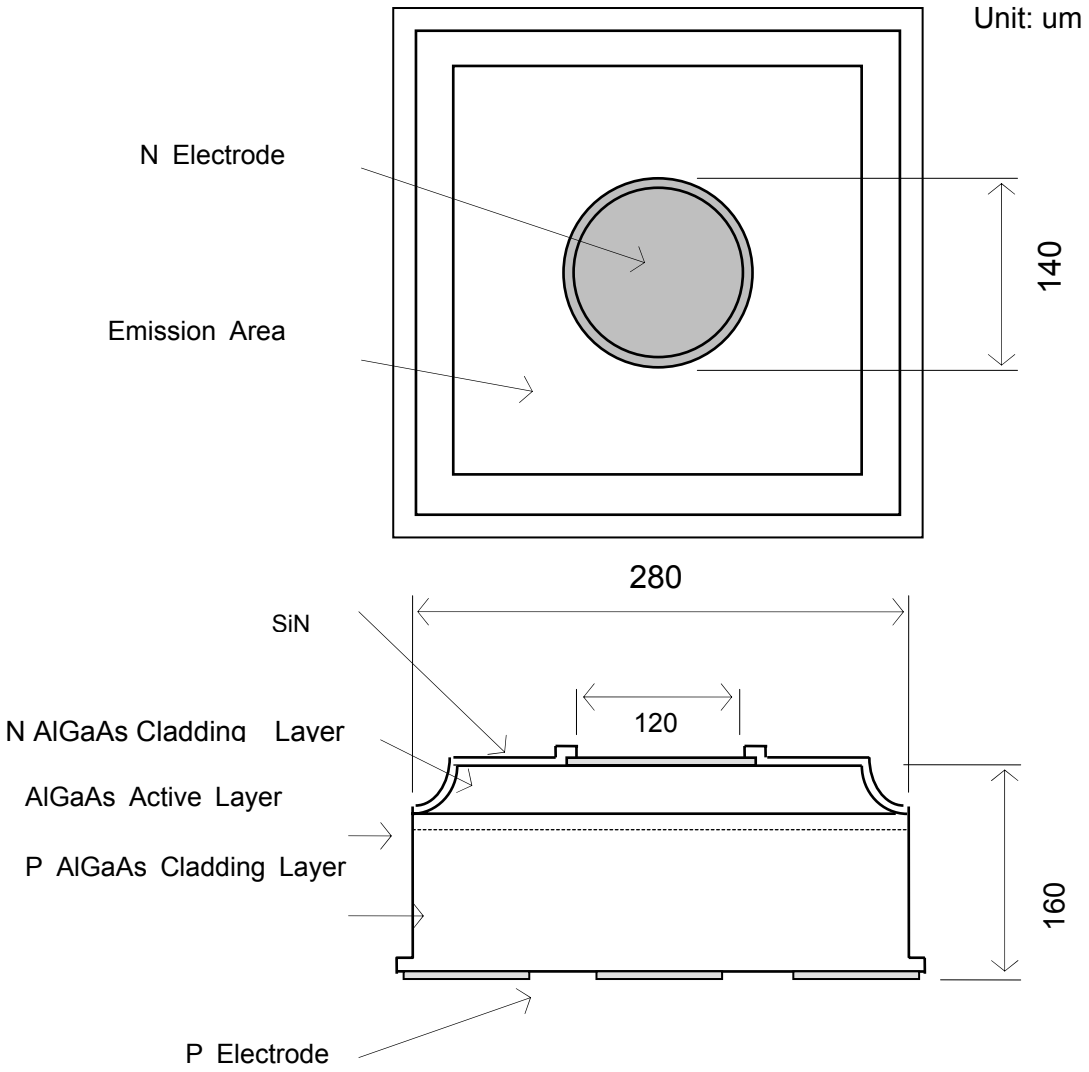
Physical Dimensions

Model YL-C660nM-35mcd



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.